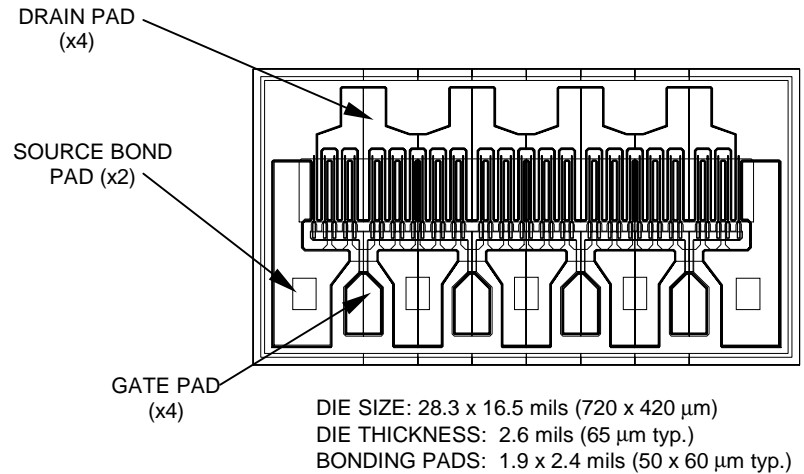


FEATURES

- +33.5 dBm Typical Power at 18 GHz
- 7 dB Typical Power Gain at 18 GHz
- +30.5 dBm at 3.3V Battery Voltage
- Low Intermodulation Distortion
- 45% Power-Added-Efficiency at 18 GHz



DESCRIPTION AND APPLICATIONS

The LP3000 is an Aluminum Gallium Arsenide / Indium Gallium Arsenide (AlGaAs/InGaAs) Pseudomorphic High Electron Mobility Transistor (PHEMT), utilizing an Electron-Beam direct-write 0.25 μm by 3000 μm Schottky barrier gate. The recessed “mushroom” gate structure minimizes parasitic gate-source and gate resistances. The epitaxial structure and processing have been optimized for reliable high-power applications. The LP3000 also features Si_3N_4 passivation and is available with plated source via-holes (LPV 3000) as an option for improved high-frequency performance. Also available in a ceramic flanged package (P100) and ball grid array package.

Typical applications include commercial and military high-performance power amplifiers, including SATCOM uplink transmitters, PCS/Cellular low-voltage high-efficiency output amplifiers, and medium-haul digital radio transmitters. The LPV 3000/LP 3000 may be procured in a variety of grades, depending upon specific user requirements. Standard lot screening is patterned after MIL-STD-19500, JANC grade. Space-level screening to FSS JANS grade is also available.

PERFORMANCE SPECIFICATIONS ($T_A = 25^\circ\text{C}$)

SYMBOLS	PARAMETERS	MIN	TYP	MAX	UNITS
I_{DSS}	Saturated Drain-Source Current $V_{\text{DS}} = 2\text{V}$ $V_{\text{GS}} = 0\text{V}$	800	1060	1100	mA
$P_{1\text{dB}}$	Output Power at 1dB Gain Compression $V_{\text{DS}} = 8.0\text{V}$, $I_{\text{DS}} = 50\% I_{\text{DSS}}$ (LP, LPV) $f = 18\text{ GHz}$	33.0	33.5		dBm
$G_{1\text{dB}}$	Power Gain at 1dB Gain Compression $V_{\text{DS}} = 8.0\text{V}$, $I_{\text{DS}} = 50\% I_{\text{DSS}}$ (LP) $f = 18\text{ GHz}$	4.0	6.0		dB
	$V_{\text{DS}} = 8.0\text{V}$, $I_{\text{DS}} = 50\% I_{\text{DSS}}$ (LPV) $f = 18\text{ GHz}$	6.0	7.0		dB
η_{ADD}	Power-Added Efficiency (typ. for Class A operation)		45		%
I_{MAX}	Maximum Drain-Source Current $V_{\text{DS}} = 2\text{V}$ $V_{\text{GS}} = +1\text{V}$		1700		mA
G_{M}	Transconductance $V_{\text{DS}} = 2\text{V}$ $V_{\text{GS}} = 0\text{V}$	725	900		mS
V_{P}	Pinch-Off Voltage $V_{\text{DS}} = 2\text{V}$ $I_{\text{DS}} = 10\text{mA}$	-0.25	-1.2	-2.0	V
I_{GSO}	Gate-Source Leakage Current $V_{\text{GS}} = -5\text{V}$		15	125	μA
BV_{GS}	Gate-Source Breakdown Voltage $I_{\text{GS}} = 15\text{mA}$	-12	-15		V
BV_{GD}	Gate-Drain Breakdown Voltage $I_{\text{GD}} = 15\text{mA}$	-12	-16		V
Θ_{J}	Thermal Resistivity		20		$^\circ\text{C/W}$

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ABSOLUTE MAXIMUM RATINGS (25°C)		
SYMBOL	PARAMETER	RATING ¹
V _{DS}	Drain-Source Voltage	12V
V _{GS}	Gate-Source Voltage	-5V
I _{DS}	Drain-Source Current	2 x I _{DSS}
I _G	Gate Current	120 mA
P _{IN}	RF Input Power	1.2 W
T _{CH}	Channel Temperature	175°C
T _{STG}	Storage Temperature	-65/175°C
P _T	Power Dissipation	6.0W ^{3,4}

RECOMMENDED CONTINUOUS OPERATING LIMITS		
SYMBOL	PARAMETER	RATING ²
V _{DS}	Drain-Source Voltage	8V
V _{GS}	Gate-Source Voltage	-1V
I _{DS}	Drain-Source Current	0.8 x I _{DSS}
I _G	Gate Current	40 mA
P _{IN}	RF Input Power	600 mW
T _{CH}	Channel Temperature	150°C
T _{STG}	Storage Temperature	-20/50°C
P _T	Power Dissipation	5.0 W ^{3,4}
G _{XdB}	Gain Compression	8 dB

NOTES:

- Operating conditions that exceed the Absolute Maximum Ratings could result in permanent damage to the device.
- Recommended Continuous Operating Limits should be observed for reliable device operation.
- Power Dissipation defined as: $P_T \equiv (P_{DC} + P_{IN}) - P_{OUT}$, where: P_{DC} = DC bias power, P_{OUT} = RF output power, and P_{IN} = RF input power.
- Power Dissipation to be de-rated as follows:
- Specifications subject to change without notice.

Example #1 :

V_{DS} = 8V, I_{DS} = 535 mA

P_{IN} = P_{OUT} = 0 dBm (quiescent condition):

P_T = P_{DC} = 4.28W

Max. continuous T_{HS} = 25°C

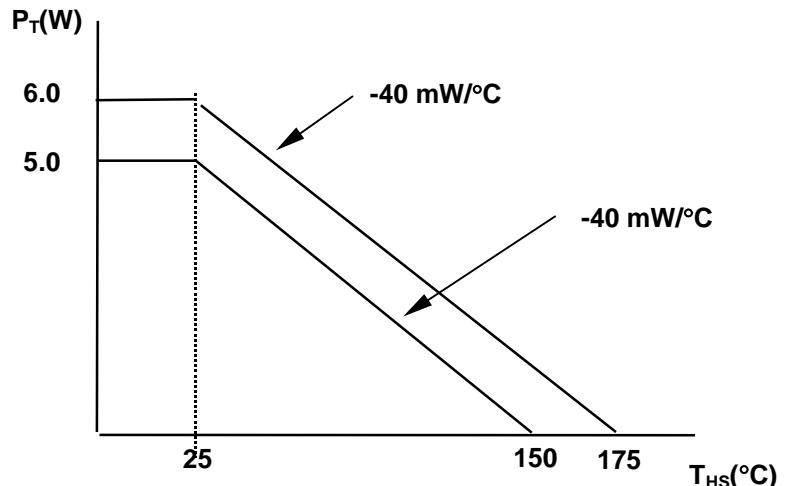
Example #2:

V_{DS} = 8V, I_{DS} = 535 mA

P_{IN} = 26.5 dBm P_{OUT} = 33.5 dBm

P_T = (4.28+0.45) - 2.24 = 2.49W

Max. continuous T_{HS} = 88°C


HANDLING PRECAUTIONS:

PHEMT chips should be stored in a dry nitrogen environment until assembly. Care should be exercised during handling to avoid damage to the devices. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. These devices should be treated as Class 1A (0-500V), and further information on ESD control measures can be found in MIL-STD-1686 and MIL-HDBK-263.

ASSEMBLY INSTRUCTIONS:

The recommended die attach is gold/tin eutectic solder under a nitrogen atmosphere. Stage temperature should be 280-290°C; maximum time at temperature is 1 min. The recommended wire bond method is thermo-compression wedge bonding with 0.7 or 1.0 mil (0.018 or 0.025 mm) gold wire. Stage temperature should be 250-260°C.

APPLICATIONS NOTES AND DESIGN DATA:

Applications Notes are available from your local FSS Sales Representative, or directly from the factory. Complete design data, including S-parameters, Noise data, and Large-Signal models, is available on 3.5" diskette, or may be down-loaded from our Web Page.

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